Silicon N Channel MOS FET High Speed Power Switching

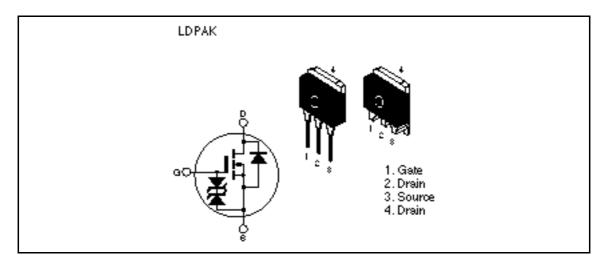
HITACHI

ADE-208-567 Target specification 1st. Edition

Features

- Low on-resistance
 - $R_{DS(on)} = 7m$ typ.
- 4V gate drive devices.
- High speed switching

Outline





Absolute Maximum Ratings (Ta = 25°C)

| Item | Symbol | Ratings | Unit | |
|---|-------------------|-------------|------|--|
| Drain to source voltage | V _{DSS} | 30 | V | |
| Gate to source voltage | V _{GSS} | ±20 | V | |
| Drain current | I _D | 50 | А | |
| Drain peak current | ↓ D(pulse) * 1 | 200 | А | |
| Body to drain diode reverse drain current | l _{DR} | 50 | А | |
| Channel dissipation | Pch* ² | 75 | W | |
| Channel temperature | Tch | 150 | °C | |
| Storage temperature | Tstg | -55 to +150 | °C | |
| | | | | |

Notes: 1. PW 10µs, duty cycle 1 %

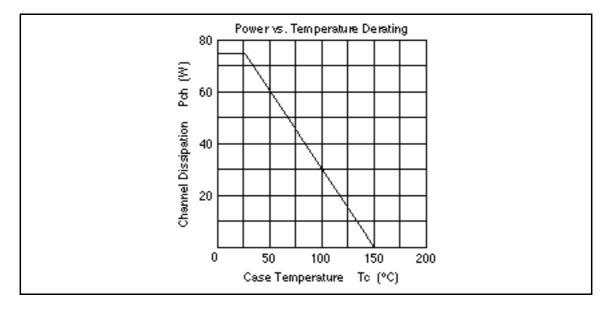
2. Value at $Tc = 25^{\circ}C$

Electrical Characteristics (Ta = 25°C)

| Item | Symbol | Min | Тур | Мах | Unit | Test Conditions |
|---|-----------------------------|-----|------|-----|------|---|
| Drain to source breakdown voltage | $V_{(\text{BR})\text{DSS}}$ | 30 | _ | _ | V | $I_{\rm D} = 10 {\rm mA}, V_{\rm GS} = 0$ |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | ±20 | _ | _ | V | $I_{G} = \pm 100 \mu A, V_{DS} = 0$ |
| Zero gate voltege drain current | I _{DSS} | _ | _ | 10 | μA | $V_{\rm DS} = 30$ V, $V_{\rm GS} = 0$ |
| Gate to source leak current | I _{GSS} | _ | _ | ±10 | μA | $V_{GS} = \pm 16V, V_{DS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 1.0 | _ | 2.0 | V | $I_{\rm D} = 1$ mA, $V_{\rm DS} = 10$ V |
| Static drain to source on state | $R_{\text{DS(on)}}$ | _ | 7.0 | 10 | m | $I_{\rm D} = 25$ A, $V_{\rm GS} = 10$ V ^{*1} |
| resistance | R _{DS(on)} | _ | 12 | 18 | m | $I_{\rm D} = 25$ A, $V_{\rm GS} = 4$ V ^{*1} |
| Forward transfer admittance | y _{fs} | 25 | 45 | _ | S | $I_{\rm D} = 25$ A, $V_{\rm DS} = 10$ V ^{*1} |
| Input capacitance | Ciss | _ | 2000 | _ | pF | $V_{DS} = 10V$ |
| Output capacitance | Coss | _ | 1500 | | pF | $V_{GS} = 0$ |
| Reverse transfer capacitance | Crss | _ | 350 | | pF | f = 1MHz |
| Turn-on delay time | t _{d(on)} | _ | 20 | | ns | $V_{GS} = 10V, I_{D} = 25A$ |
| Rise time | t, | — | 330 | | ns | $R_{L} = 0.4$ |
| Turn-off delay time | $t_{d(off)}$ | _ | 190 | | ns | _ |
| Fall time | t _f | _ | 190 | | ns | |
| Body to drain diode forward voltage | V_{DF} | _ | 0.95 | | V | $I_{\rm D} = 50$ A, $V_{\rm GS} = 0$ |
| Body to drain diode reverse recovery time | t _{rr} | _ | 140 | | ns | I _F = 50A, V _{GS} = 0 diF/ dt = 50A/μs |
| | | | | | | $ur = 50A/\mu S$ |

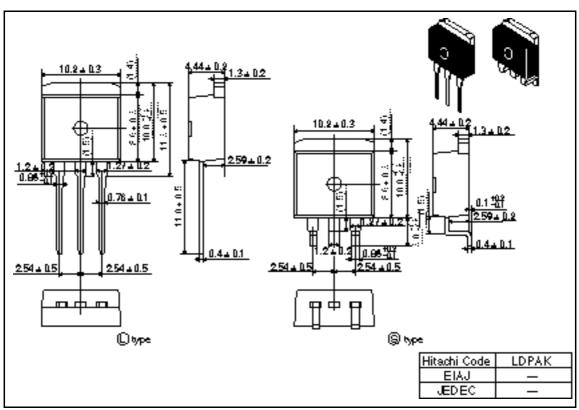
Note: 1. Pulse test

Main Characteristics



Package Dimensions





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